EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	134/33,94.1,95.2,137,149.ccls. and (((substrate wafer semiconductor workpiece) near5 (rins$3 wash$3 clean$3)) and ((surface area region) near5 ("both" mixed) near5 (hydrophobic and hydrophilic))).clm.	US-PGPUB	OR	ON	2010/12/14 10:41
L2	1	134/33,94.1,95.2,137,149.ccls. and (((substrate wafer semiconductor workpiece) and (rins$3 wash$3 clean $3)) and ((surface area region) and ("both" mixed) and (hydrophobic and hydrophilic)).clm.	US-PGPUB	OR	ON	2010/12/14 10:42
L3	1	134/33,94.1,95.2,137,149.ccls. and ((substrate wafer semiconductor workpiece) and (rins$3 wash$3 clean $3) and (surface area region) and hydrophobic and hydrophilic and water).clm.	US-PGPUB	OR	ON	2010/12/14 10:45
S1	1	"20070131256".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 14:52
S2	2	("20080173333" | "5997653").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 14:53
S3	1	S1 and (hydrophobic hydrophilic)	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 15:24
S4	2	S2 and (hydrophobic hydrophilic)	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 15:24
S5	1	"20030084925".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 15:26
S6	0	S2 and S5	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 15:26
S7	3	S2 S5	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 15:26
S8	3	S7 and (hydrophobic hydrophilic)	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 15:26
S9	1006	((hydrophobic and hydrophilic) same (substrate wafer semiconductor workpiece)) and ((rins$3 wash$3 clean$3) same (water near3 (pure$2 purif$3 purificatiom demin demineraliz$5)))	US-PGPUB; USPAT	OR	ON	2010/05/07 15:34
S10	728	S9 and water same film	US-PGPUB; USPAT	OR	ON	2010/05/07 15:36
S11	564	S10 and water same (reduc$3 less lessen$3 small$2)	US-PGPUB; USPAT	OR	ON	2010/05/07 15:37

S12	141	S11 and water same (reduc$3 less lessen$3 small$2) same (mov$3 rotat $3)	US-PGPUB; USPAT	OR	ON	2010/05/07 15:38
S13	114	S12 and water same (suppl$4 feed$3 using use$1) same (reduc$3 less lessen$3 small$2) same (mov$3 rotat $3)	US-PGPUB; USPAT	OR	ON	2010/05/07 15:39
S14	29	S13 and water same (suppl$4 feed$3 using use$1) same (reduc$3 less lessen$3 small$2) same (mov$3 rotat $3) same film	US-PGPUB; USPAT	OR	ON	2010/05/07 15:39
S15	1	"20030084925".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 17:39
S16	1	S15 and (hydrophobic hydrophilic)	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 17:39
S17	1006	((hydrophobic and hydrophilic) same (substrate wafer semiconductor workpiece)) and ((rins$3 wash$3 clean$3) same (water near3 (pure$2 purif$3 purificatiom demin demineraliz$5)))	US-PGPUB; USPAT	OR	ON	2010/05/07 17:41
S18	182	S17 and (surface area) same ("both") same (hydrophobic and hydrophilic)	US-PGPUB; USPAT	OR	ON	2010/05/07 17:41
S19	21	S18 and (surface area) near5 ("both") near5 (hydrophobic and hydrophilic)	US-PGPUB; USPAT	OR	ON	2010/05/07 17:42
S20	6	("5882433" | "6221168" | "6398975" | "6406551" | "6491764").PN. OR ("7011715").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 17:48
S21	4	S20 and (hydrophobic and hydrophilic)	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 17:48
S22	189	S17 and (surface area region) same ("both") same (hydrophobic and hydrophilic)	US-PGPUB; USPAT	OR	ON	2010/05/07 17:50
S23	397	((substrate wafer semiconductor workpiece) near5 (rins$3 wash$3 clean$3)) and ((surface area region) near5 ("both" mixed) near5 (hydrophobic and hydrophilic))	US-PGPUB; USPAT	OR	ON	2010/05/07 17:52
S24	90	S23 and ((substrate wafer semiconductor workpiece) near5 (rins $3 wash$3 clean$3) near5 water)	US-PGPUB; USPAT	OR	ON	2010/05/07 17:53
S25	1	"6058945".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 22:51
S26	2	"2003197590".pn.	FPRS; EPO; JPO; DERWENT	OR	ON	2010/05/08 01:15
S27	64	(hydrophobic and hydrophilic) and (substrate wafer semiconductor workpiece) and (rins$3 wash$3 clean $3) and (water near3 (pure$2 purif $3 purificatiom demin demineraliz $5))	FPRS; EPO; JPO; DERWENT	OR	ON	2010/05/08 01:22

S28	22	S27 and (surface area region) and ("both" mixed)	FPRS; EPO; JPO; DERWENT	OR	ON	2010/05/08 01:24
S29	61	S27 and (surface area region)	FPRS; EPO; JPO; DERWENT	OR	ON	2010/05/08 01:24
S30	1	"20070131256".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 16:37
S31	4	("20030075204" | "20080173333" | "5997653" | "6058945").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 16:38
S32	1	S30 and (hydrophobic hydrophilic)	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 17:03
S33	1	S30 and thin$4	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 17:13
S34	1	S30 and stop$4	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 17:16
S35	1	S30 and transition$3	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 17:20
S36	1	S30 and rotat$4 same (transition$3 rins$3)	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 17:21
S37	1	S30 and rotat$4 same (transition$3 spin$4)	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 17:23
S38	414	((substrate wafer semiconductor workpiece) near5 (rins$3 wash$3 clean$3)) and ((surface area region) near5 ("both" mixed) near5 (hydrophobic and hydrophilic))	US-PGPUB; USPAT	OR	ON	2010/12/13 17:28
S39	99	S38 and ((substrate wafer semiconductor workpiece) near5 (rins $3 wash$3 clean$3) near5 water)	US-PGPUB; USPAT	OR	ON	2010/12/13 17:29
S40	1	((substrate wafer semiconductor workpiece) near5 (rinse rinsing rinsed wash washing washed clean cleaning cleaned)) and ((surface area region) near5 ("both" mixed) near5 (hydrophobic and hydrophilic))	USOCR	OR	ON	2010/12/13 17:29
S41	65	(hydrophobic and hydrophilic) and (substrate wafer semiconductor workpiece) and (rins$3 wash$3 clean $3) and (water near3 (pure$2 purif $3 purificatiom demin demineraliz $5))	FPRS; EPO; JPO; DERWENT	OR	ON	2010/12/13 17:30
S42	23	S41 and (surface area region) and ("both" mixed)	FPRS; EPO; JPO; DERWENT	OR	ON	2010/12/13 17:30
S43	123	S39 S40 S42	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2010/12/13 17:31

S44	93	S43 and (((film layer$3 coat$3) near5 (thin$3 less$2 small$3 decreas $3 reduc$3)) or ((feed$3 flow$3 flowrate suppl$4) near5 (less$2 small $3 decreas$3 reduc$3)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2010/12/13 17:34
S45	1	"20020130106".PN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 18:18
S46	5	S31 S45	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 18:18
S47	0	("2008/0173333").URPN.	USPAT	OR	ON	2010/12/13 18:18
S48	11	("2003/0075204").URPN.	USPAT	OR	ON	2010/12/13 18:18
S49	2	("2002/0130106").URPN.	USPAT	OR	ON	2010/12/13 18:18
S50	18	("3893869" | "4927781" | "5331180" | "5372962" | "5427977" | "5510633" | "5626159").PN. OR ("6058945"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 18:19
S51	107	("4027686" | "4871417" | "5248380" | "5351360" | "5372652" | "5456758" | "5558110").PN. OR ("5997653"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 18:19
S52	132	S47 S48 S49 S50 S51	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 18:19
S53	63	S52 and ((substrate wafer semiconductor workpiece) near5 (rins $3 wash$3 clean$3) near5 water)	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 18:19
S54	1	S52 and ((substrate wafer semiconductor workpiece) near5 (rins $3 wash$3 clean$3)) and ((surface area region) near5 ("both" mixed) near5 (hydrophobic and hydrophilic))	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 18:20

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